

Hiroaki Ohta

List of Publications by Year in descending order

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40
papers

1,757
citations

279701

23
h-index

360920

35
g-index

40
all docs

40
docs citations

40
times ranked

1250
citing authors

#	ARTICLE	IF	CITATIONS
1	Vertical GaN-Based Trench Gate Metal Oxide Semiconductor Field-Effect Transistors on GaN Bulk Substrates. Applied Physics Express, 2008, 1, 011105.	1.1	186
2	Continuous-Wave Operation of m-Plane InGaN Multiple Quantum Well Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L187-L189.	0.8	143
3	Dislocation-Free m-Plane InGaN/GaN Light-Emitting Diodes on m-Plane GaN Single Crystals. Japanese Journal of Applied Physics, 2006, 45, L1197-L1199.	0.8	127
4	Partial strain relaxation via misfit dislocation generation at heterointerfaces in (Al,In)GaN epitaxial layers grown on semipolar (112̄2) GaN free standing substrates. Applied Physics Letters, 2009, 95, .	1.5	98
5	GaN-Based Trench Gate Metal Oxide Semiconductor Field Effect Transistors with Over 100 cm ² /(V s) Channel Mobility. Japanese Journal of Applied Physics, 2007, 46, L599-L601.	0.8	80
6	Temperature dependence of polarized photoluminescence from nonpolar m-plane InGaN multiple quantum wells for blue laser diodes. Applied Physics Letters, 2008, 92, .	1.5	78
7	30-mW-Class High-Power and High-Efficiency Blue Semipolar (10̄11̄r1) InGaN/GaN Light-Emitting Diodes Obtained by Backside Roughening Technique. Applied Physics Express, 2010, 3, 102101.	1.1	77
8	Stacking fault formation in the long wavelength InGaN/GaN multiple quantum wells grown on m-plane GaN. Applied Physics Letters, 2010, 96, .	1.5	74
9	Future of group-III nitride semiconductor green laser diodes [Invited]. Journal of the Optical Society of America B: Optical Physics, 2010, 27, B45.	0.9	63
10	High Quality InGaN/AlGaIn Multiple Quantum Wells for Semipolar InGaN Green Laser Diodes. Applied Physics Express, 2010, 3, 082001.	1.1	62
11	Optical waveguide simulations for the optimization of InGaN-based green laser diodes. Journal of Applied Physics, 2010, 107, .	1.1	57
12	Continuous-Wave Operation of Blue Laser Diodes Based on Nonpolar m-Plane Gallium Nitride. Applied Physics Express, 2008, 1, 011102.	1.1	56
13	Blue-Green InGaN/GaN Laser Diodes on Miscut c̄m̄-Plane GaN Substrate. Applied Physics Express, 0, 2, 082102.	1.1	56
14	GaN-Based Integrated Lateral Thermoelectric Device for Micro-Power Generation. Applied Physics Express, 2009, 2, 111003.	1.1	54
15	High temperature thermoelectric properties of optimized InGaN. Journal of Applied Physics, 2011, 110, .	1.1	53
16	Pure Blue Laser Diodes Based on Nonpolar m-Plane Gallium Nitride with InGaN Waveguiding Layers. Japanese Journal of Applied Physics, 2007, 46, L820-L822.	0.8	50
17	Temperature dependence of polarized electroluminescence from nonpolar m-plane InGaN-based light emitting diodes. Applied Physics Letters, 2007, 91, 171110.	1.5	43
18	Characteristics of Polarized Electroluminescence from m-plane InGaN-based Light Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, L1010-L1012.	0.8	40

#	ARTICLE	IF	CITATIONS
19	m-Plane GaN-Based Blue Superluminescent Diodes Fabricated Using Selective Chemical Wet Etching. Applied Physics Express, 2009, 2, 121004.	1.1	40
20	Nonpolar AlGaIn-Cladding-Free Blue Laser Diodes with InGaIn Waveguiding. Applied Physics Express, 0, 2, 071003.	1.1	37
21	Plasma-surface interactions for advanced plasma etching processes in nanoscale ULSI device fabrication: A numerical and experimental study. Thin Solid Films, 2010, 518, 3461-3468.	0.8	31
22	InGaIn/GaN Blue Laser Diode Grown on Semipolar (30ar31) Free-Standing GaN Substrates. Applied Physics Express, 2010, 3, 052702.	1.1	27
23	Continuous-Wave Operation of Pure Blue AlGaIn-Cladding-Free Nonpolar InGaIn/GaN Laser Diodes. Applied Physics Express, 2010, 3, 092103.	1.1	27
24	Nonpolar/Semipolar GaN Technology for Violet, Blue, and Green Laser Diodes. MRS Bulletin, 2009, 34, 324-327.	1.7	25
25	Electroluminescence Characterization of (2021) InGaIn/GaN Light Emitting Diodes with Various Wavelengths. Japanese Journal of Applied Physics, 2010, 49, 070203.	0.8	23
26	m-plane pure blue laser diodes with p-GaN/n-AlGaIn-based asymmetric cladding and InGaIn-based wave-guiding layers. Applied Physics Letters, 2009, 95, 081110.	1.5	20
27	Vertical Stand Transparent Light-Emitting Diode Architecture for High-Efficiency and High-Power Light-Emitting Diodes. Japanese Journal of Applied Physics, 2010, 49, 080210.	0.8	20
28	Optimization of Device Structures for Bright Blue Semipolar (1011) Light Emitting Diodes via Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2010, 49, 070206.	0.8	19
29	Molecular Dynamics Simulation of Si Etching by Off-Normal Cl+ Bombardment at High Neutral-to-Ion Flux Ratios. Japanese Journal of Applied Physics, 2008, 47, 8560-8564.	0.8	15
30	An Improvement of Stillinger-Weber Interatomic Potential Model for Reactive Ion Etching Simulations. Japanese Journal of Applied Physics, 2009, 48, 020225.	0.8	14
31	Numerical Investigation on Origin of Microscopic Surface Roughness during Si Etching by Chemically Reactive Plasmas. Japanese Journal of Applied Physics, 2008, 47, 6464-6466.	0.8	13
32	High Power and High Efficiency Blue InGaIn Light Emitting Diodes on Free-Standing Semipolar (30ar3ar1) Bulk GaN Substrate. Japanese Journal of Applied Physics, 2010, 49, 080203.	0.8	12
33	Molecular-Dynamics-Based Profile Evolution Simulation for Sub-10-nm Si Processing Technology. Applied Physics Express, 2009, 2, 116501.	1.1	12
34	Numerical Study on Si Etching by Monatomic Br+/Cl+ Beams and Diatomic Br2+/Cl2+/HBr+ Beams. Japanese Journal of Applied Physics, 2009, 48, 070219.	0.8	8
35	Propagation of Spontaneous Emission in Birefringent m-Axis Oriented Semipolar (11ar22) (Al,In,Ga)N Waveguide Structures. Japanese Journal of Applied Physics, 2010, 49, 010207.	0.8	7
36	Reduction in threshold voltages in GaN-based metal oxide semiconductor field effect transistors. Applied Physics Letters, 2008, 92, 243505.	1.5	5

#	ARTICLE	IF	CITATIONS
37	Field and polarity dependence of time-to-resistance increase in Fe ²⁺ O films studied by constant voltage stress method. Applied Physics Letters, 2009, 94, 013507.	1.5	5
38	Simulation and experimental study on the characteristics of plasma-induced damage and methodology for accurate damage analysis. , 2009, , .		0
39	The low leakage current in floating body GaN metal oxide semiconductor field effect transistors. Solid-State Electronics, 2010, 54, 1561-1565.	0.8	0
40	GaN-Based Optical Devices. , 2011, , 69-86.		0